

*Schematic components that have been frozen by the user will appear with blue reference designators.*

## Power Supply Input

Var	Value	Units	Description
VACMIN	170	V	Minimum Input AC Voltage (Manual Overwrite)
VACMAX	270	V	Maximum Input AC Voltage (Manual Overwrite)
FL	50	Hz	Line Frequency (Manual Overwrite)
TC	2.07	ms	Input Rectifier Conduction Time
Z	0.70		Loss Allocation Factor
$\eta$	80.0	%	Efficiency Estimate (Target)
VMIN	89.5	V	Minimum DC Input Voltage
VMAX	381.8	V	Maximum DC Input Voltage

## Input Section

Var	Value	Units	Description
Fuse	3.00	A	Input Fuse Rated Current
I <sub>AVG</sub>	2.38	A	Average Diode Bridge Current (DC Input Current)
Thermistor	3.30	$\Omega$	Input Thermistor

## Device Variables

Var	Value	Units	Description
Device	TOP271EG		PI Device Name (Manual Overwrite).
BVDSS	725	V	Drn-Src Bkdn Voltage
Current Limit Mode	Default		Device Current Limit Mode
OVP_FLAG	NO		Output Overvoltage Protection Enabled
PO	295.07	W	Total Output Power
VDRAIN Estimated	578.93	V	Estimated Drain Voltage
VDS	10.00	V	On state Drain to Source Voltage
FS	132000	Hz	Switching Frequency (at VMIN and Full Load)
KP	0.655		Continuous/Discontinuous Operating Ratio (at VMIN and Full Load)
DMAX	0.569		Maximum Duty Cycle (at VMIN and Full Load)
KI	1.00		Current Limit Reduction Factor (Manual Overwrite)
ILIMITEXT	4.81	A	Programmed Current Limit
ILIMITMIN	4.808	A	Minimum Current Limit
ILIMITMAX	5.532	A	Maximum Current Limit
PLIM_FLAG	NO		Enable Overload Power Limiting
IP	6.219	A	<b>Peak Primary Current (at VMIN and Full Load).</b>
IRMS	3.280	A	Primary RMS Current (at VMIN and Full Load)
RTH_DEVICE	3.30	$^{\circ}\text{C}/\text{W}$	PI Device Heatsink Maximum Thermal Resistance
DEV_HSINK_TYPE	Aluminum Extruded		PI Device Heatsink Type
DEV_HSINK_PN	530002B02500G		PI Device (Extruded) Heatsink Part Number

## Clamp Circuit

Var	Value	Units	Description
Clamp Type	RCD + Zener Clamp		Clamp Circuit Type
VCLAMP	97.09	V	Average Clamping Voltage
Estimated Clamp Loss	5.395	W	Clamp total power loss
VC_MARGIN	143.16	V	Clamp Voltage Safety Margin

## Primary Bias Variables

Var	Value	Units	Description
VB	12.0	V	Bias Voltage
IB	0.006	A	Bias Current
PIVB	60	V	Bias Rectifier Maximum Peak Inverse Voltage
NB	8		Primary Bias Winding Number of Turns

## Transformer Construction Parameters

Var	Value	Units	Description
Core Type	ETD44/22/15		Core Type
Core Material	3F3		Core Material
Bobbin Reference	Generic, 9 pri. + 9 sec.		Bobbin Reference
Bobbin Orientation	Horizontal		Bobbin type
Primary Pins	6		Number of Primary pins used
Secondary Pins	2		Number of Secondary pins used
USE_SHIELDS	NO		Use shield Windings
LP_nom	165	$\mu$ H	Nominal Primary Inductance
LP_Tol	10.0	%	Primary Inductance Tolerance
NP	63.4		Calculated Primary Winding Total Number of Turns
NSM	36		Secondary Main Number of Turns
CMA	492.76	Cmils/A	Primary Winding Current Capacity
VOR	100.00	V	Reflected Output Voltage
BW	29.50	mm	Bobbin Winding Width
ML	0.00	mm	Safety Margin on Left Width
MR	0.00	mm	Safety Margin on Right Width
FF	114.17	%	<b>Actual Transformer Fit Factor. 100% signifies fully utilized winding window.</b>
AE	173.00	mm <sup>2</sup>	Core Cross Sectional Area
ALG	37	nH/T <sup>2</sup>	Gapped Core Specific Inductance
BM	840	Gauss	Maximum Flux Density
BP	823	Gauss	<b>Peak Flux Density.</b>
BAC	275	Gauss	AC Flux Density for Core Loss
LG	5.838	mm	<b>Estimated Gap Length.</b>
L_LKG	2.47	$\mu$ H	Estimated primary leakage inductance
LSEC	20	nH	Secondary Trace Inductance

## Primary Winding Section 1

Var	Value	Units	Description
NP1	39		Number of Primary Winding Turns in the First Section of Primary
Wire Size	24	AWG	Primary Winding - Wire Size
Winding Type	Quadfilar (x4)		Primary Winding - Number of Parallel Wire Strands
L	3.00		Primary Winding - Number of Layers
DC Copper Loss	0.63	W	Primary Section 1 DC Losses

## Primary Winding Section 2

Var	Value	Units	Description
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NP2	25		Rounded (Integer) Number of Primary winding turns in the second section of primary
Wire Size	24	AWG	Primary Winding - Wire Size
Winding Type	Quadfilar (x4)		Primary Winding - Number of Parallel Wire Strands
L2	1.92		Primary Number of Layers in 2nd split winding

## Output 1

Var	Value	Units	Description
VO	58.00	V	Typical Output Voltage
IO	5.00	A	Output Current
VOUT_ACTUAL	58.00	V	Actual Output Voltage
NS	36		Secondary Number of Turns
Wire Size	24	AWG	Wire size of secondary winding
Winding Type	Trifilar (x3)		Output winding number of parallel strands
L_S_OUT	2.75		Secondary Output Winding Layers
DC Copper Loss	2.42	W	Secondary DC Losses
VD	1.70	V	Output Winding Diode Forward Voltage Drop
VD	1.70	V	Output Winding Diode Forward Voltage Drop
PIVS	272.78	V	Output Rectifier Maximum Peak Inverse Voltage
ISP	10.772	A	Peak Secondary Current
ISRMS	4.939	A	Secondary RMS Current
ISRMS_WINDING	4.939	A	Secondary Winding RMS Current
CMAS	245	Cmils/A	Secondary Winding Current Capacity
RTH_RECTIFIER	6.35	°C/W	Output Rectifier Heatsink Maximum Thermal Resistance
OR_HSINK_TYPE	Aluminum Extruded		Output Rectifier Heatsink Type
OR_HSINK_PN	533402B02552G		Output Rectifier (Extruded) Heatsink Part Number
CO	0 x 1	µF	Output Capacitor - Capacitance
IRIPPLE	0.000	A	Output Capacitor - RMS Ripple Current
Expected Lifetime	8000	hr	Output Capacitor - Expected Lifetime

## Feedback Circuit

Var	Value	Units	Description
DUAL_OUTPUT_FB_FLAG	NO		Get feedback from 2 outputs
SF_FLAG	NO		Soft Finish Circuits use flag
TYPE_3CTRL_FLAG	NO		Phase Boost Network flag

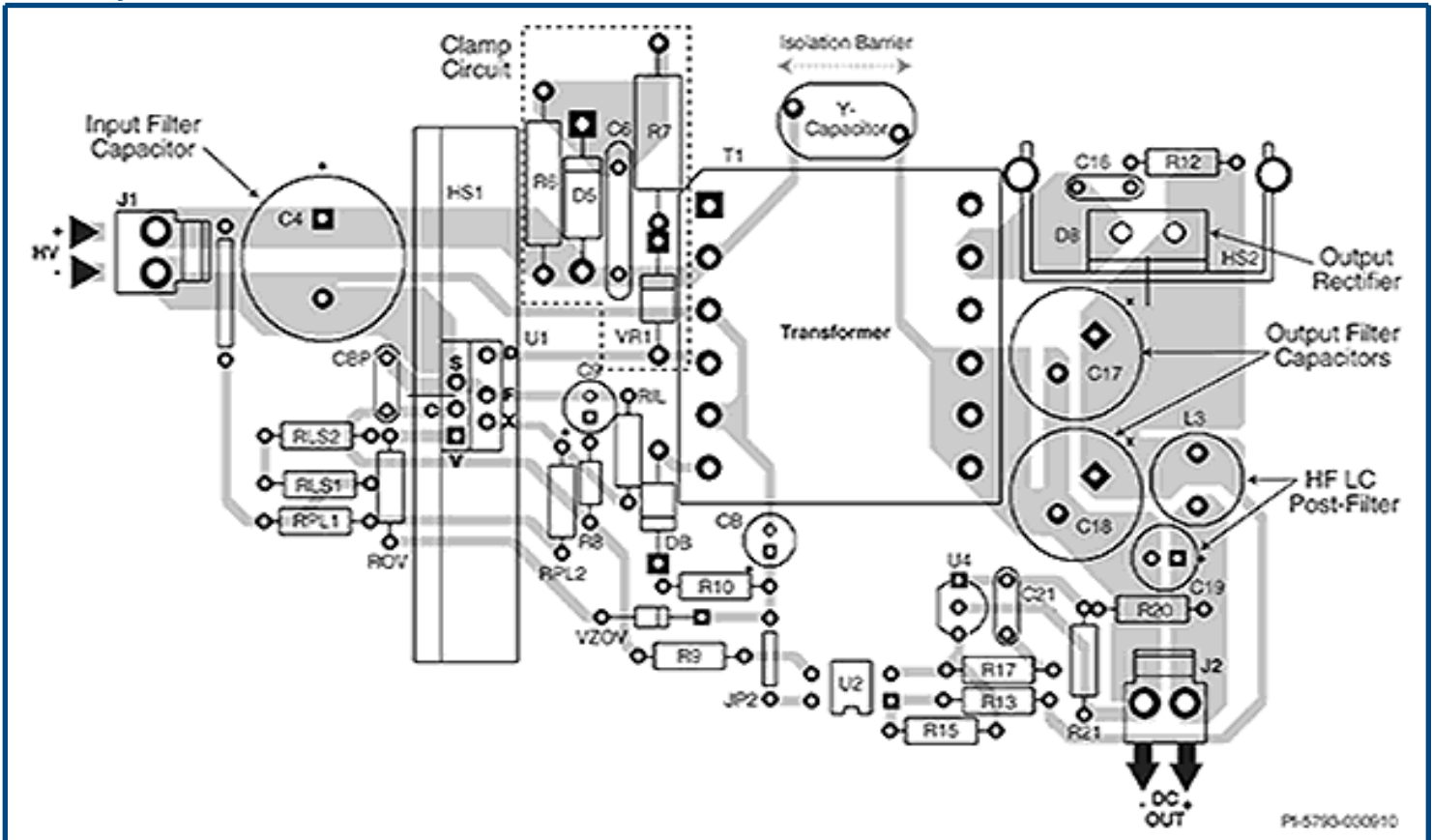
High output current Flyback design.

Use parallel low ESR output capacitors, reduce secondary ripple currents by reducing VOR and KP.

The regulation and tolerances do not account for thermal drifting and component tolerance of the output diode forward voltage drop and voltage drops across the LC post filter. The actual voltage values are estimated at full load only.

Please verify cross regulation performance on the bench.

## Board Layout Recommendations



Click on the "Show me" icon to highlight relevant areas on the sample layout.

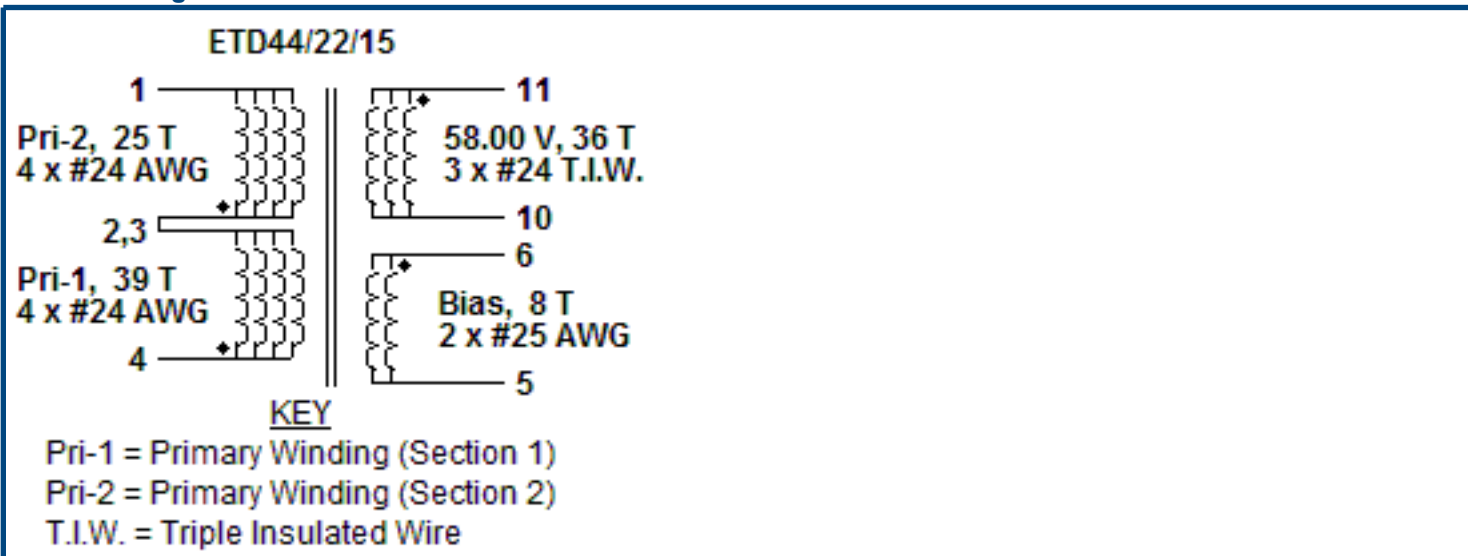
	Description	Show Me
1	Minimize loop area formed by drain, clamp and transformer	
2	Bias winding and bias capacitor are a power connection and therefore returned to Kelvin connection at SOURCE pin	
3	V and X pin node areas minimized, line sensing (R1 & R2) and power limiting (R3 & R4) close to device. Connections to V and X pin nodes should be away from noisy switching nodes (drain, clamp and bias)	
4	Place CONTROL pin decoupling capacitor directly across CONTROL and SOURCE pins	
5	Y capacitor connected between output RTN and B+	
6	Minimize loop area formed by secondary winding, the output rectifier and the output filter capacitor	
7	Kelvin connection at SOURCE pins: power and signal currents kept separate	
8	B+ connection of RLS or RPL resistor should be on input side of capacitor to prevent switching noise injection	

## Bill Of Materials

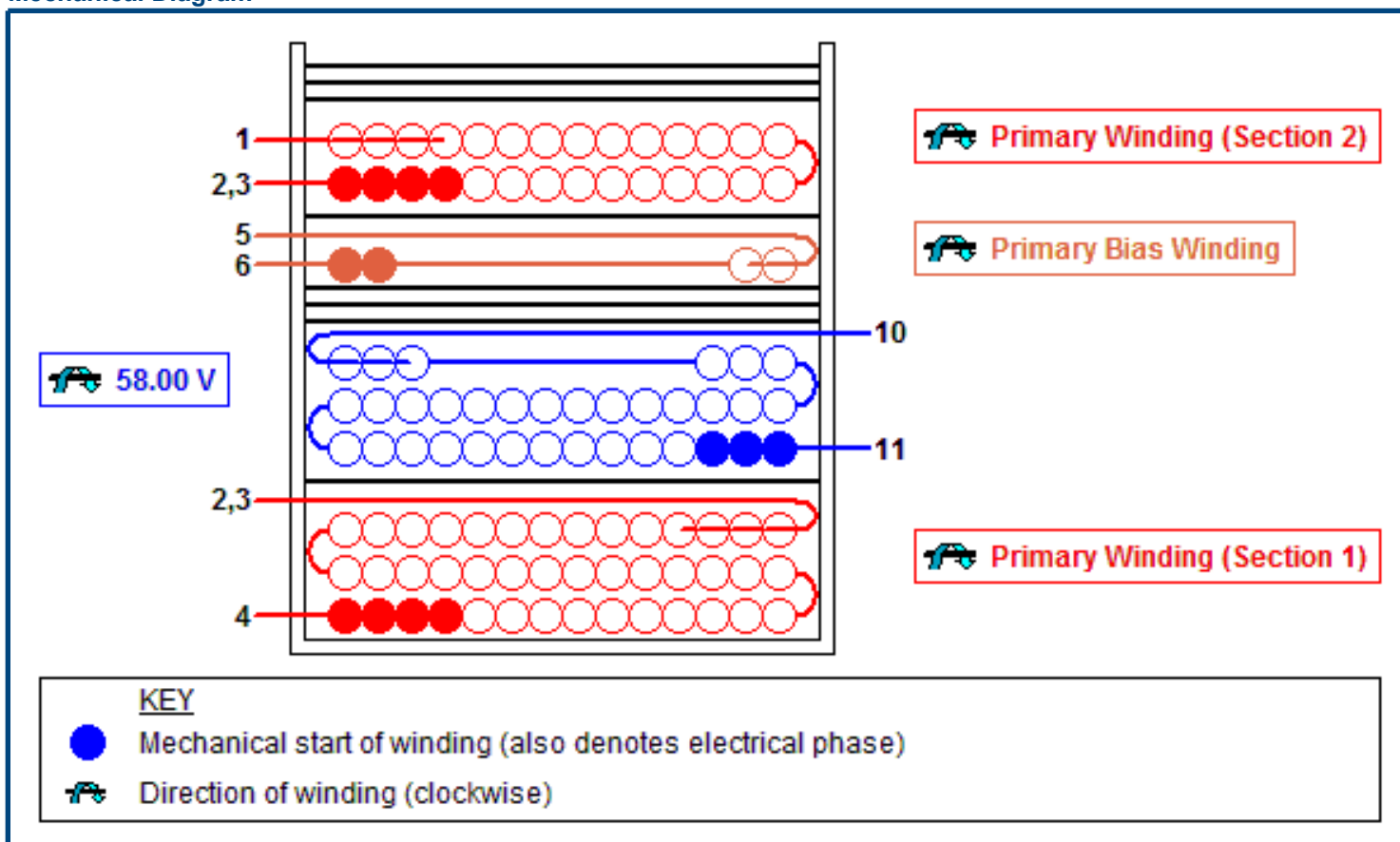
<b>Ite m #</b>	<b>Quantity</b>	<b>Part Ref</b>	<b>Value</b>	<b>Description</b>	<b>Mfg</b>	<b>Mfg Part Number</b>
1	1	BR1	PB66-BP	600 V, 6 A, Standard Recovery Bridge, PB-6	MCC	PB66-BP
2	1	C1	0.039 nF	0.039 nF, 380 VAC, Film, X Class	Vishay BCcomponents	VY1471K31Y5UQ63V0
3	1	C2	68 $\mu$ F	68 $\mu$ F, 450 V, High Voltage Al Electrolytic, (25 mm x 22 mm)	Epcos	B43644A5686M000
4	1	C3	15 nF	15 nF, 630 V, High Voltage Ceramic	TDK	CGA6L4NP02J153J160AA
5	1	C4	0.1 $\mu$ F	0.1 $\mu$ F, 16 V, Ceramic, X7R	AVX Corp	0603YC104K4T4A
6	1	C5	47 $\mu$ F	47 $\mu$ F, 10.0 V, Electrolytic, Gen Purpose, 1000 m $\Omega$ , (5.2 mm x 6.3 mm)	United Chemi-Con	EMVY100ADA470MF55G
7	1	C6	0.47 nF	0.47 nF, 440 VAC, Ceramic, Y Class	Vishay BCcomponents	VY2471K29Y5SS63V7
8	1	C7	18 pF	18 pF, 1 kV, High Voltage Ceramic	Murata	GRM31A7U3A180JW31D
9	1	C8	10 $\mu$ F	10 $\mu$ F, 50 V, Electrolytic, Gen Purpose, 1000 m $\Omega$ , (6.1 mm x 6.3 mm)	Rubycon	50TRV10M6.3X6.1
10	1	C9	0.47 $\mu$ F	0.47 $\mu$ F, 100 V, Electrolytic, Low ESR, 270 m $\Omega$ , (11 mm x 5 mm)	Nichicon	UVR2AR47MDD
11	1	C10	100 $\mu$ F	100 $\mu$ F, 100 V, Electrolytic, Low ESR, 170 m $\Omega$ , (16.5 mm x 16 mm)	Panasonic	EEE-FK2A101AM
12	1	C11	15 nF	15 nF, 50 V, Ceramic, X7R	Kemet	C0805C153K5RACTU
13	1	D1	Undefined	1000 V, 200 A, Fast Recovery, 75 ns, Undefined	-	Undefined
14	1	D2	FDLL4448	100 V, 0.3 A, Fast Recovery, 4 ns, SOD-80	ON Semiconductor	FDLL4448
15	1	D3	STTH20R04G-TR	400 V, 20 A, Ultrafast Recovery, 45 ns, D2PAK	STMicroelectronics	STTH20R04G-TR
16	1	F1	3 A	350 VAC, 3 A, Glass Cartridge, Time Lag Fuse	Bel Fuse Inc.	2JS 3-R
17	1	HS1	530002B02500G	2.6 °C/W TO-220. Heatsink for use with Device U1.	Aavid	530002B02500G
18	1	HS2	533402B02552G	5 °C/W TO-220. Heatsink for use with Rectifier D3.	Aavid	533402B02552G
19	1	L1	7 mH	7 mH, 3.5 A	Würth Elektronik	744834407
20	1	L2	3.3 $\mu$ H	3.3 $\mu$ H, 7.6 A	Bourns Inc.	PM5022-3R3M-RC
21	5	R1, R2, R3, R4, R5	36 k $\Omega$	36 k $\Omega$ , 5 %, 2 W, Metal Oxide Film	Generic	
22	1	R6	5.1 $\Omega$	5.1 $\Omega$ , 5 %, 0.25 W, Thick Film	Generic	
23	2	R7, R8	4.02 M $\Omega$	4.02 M $\Omega$ , 1 %, 0.25 W, Thick Film	Generic	
24	1	R9	6.8 $\Omega$	6.8 $\Omega$ , 5 %, 0.125 W, Thick Film	Generic	
25	1	R10	560 $\Omega$	560 $\Omega$ , 5 %, 0.5 W, Thick Film	Generic	
26	1	R11	40200 $\Omega$	40200 $\Omega$ , 1 %, 0.125 W, Thick Film	Generic	
27	1	R12	1 k $\Omega$	1 k $\Omega$ , 5 %, 0.125 W, Thick Film	Generic	
28	1	R13	255 k $\Omega$	255 k $\Omega$ , 1 %, 0.125 W, Thick Film	Generic	
29	1	R14	11.5 k $\Omega$	11.5 k $\Omega$ , 1 %, 0.125 W, Thick Film	Generic	
30	1	RT1	3.3 $\Omega$	NTC Thermistor 3.3 $\Omega$ , 4.5 A	Murata	PRG18BC3R3MM1RB

31	1	T1	ETD44/22/15	3F3 Core Material See Transformer Construction's Materials List for complete information	Epcos	B66365-G-X127
32	1	U1	TOP271EG	TOPSwitch-JX, TOP271EG, eSIP-7C	Power Integrations	TOP271EG
33	1	U2	LTV-826S	Optocoupler LTV-826S , 80 V, CTR 300 - 600 %, 4-SMD	Liteon	LTV-826S
34	1	U3	LM431ACM/NO PB	2.495 V, Shunt Regulator IC, 2 %, SOIC-8	Texas Instruments	LM431ACM/NOPB
35	1	VR1	P6SMB120CA	120 V, 5 W, 5 %, DO-214AA, TVS	Vishay	P6SMB120CA

## Electrical Diagram



## Mechanical Diagram



## Winding Instruction

### Primary Winding (Section 1)

Start on pin(s) 4 and wind 39 turns (x 4 filar) of item [5]. in 3 layer(s) from left to right. Winding direction is clockwise. At the end of 1st layer, continue to wind the next layer from right to left. At the end of 2nd layer, continue to wind the next layer from left to right. On the final layer, spread the winding evenly across entire bobbin. Finish this winding on pin(s) 2,3.

Add 1 layer of tape, item [3], for insulation.

### Secondary Winding

Start on pin(s) 11 and wind 36 turns (x 3 filar) of item [6]. Spread the winding evenly across entire bobbin. Winding direction is clockwise. Finish this winding on pin(s) 10.

Add 3 layers of tape, item [3], for insulation.

### Primary Bias Winding



Start on pin(s) 6 and wind 8 turns (x 2 filar) of item [7]. Winding direction is clockwise. Spread the winding evenly across entire bobbin. Finish this winding on pin(s) 5.

Add 1 layer of tape, item [3], for insulation.

### Primary Winding (Section 2)

Start on pin(s) 2,3 and wind 25 turns (x 4 filar) of item [5]. in 2 layer(s) from left to right. Winding direction is clockwise. At the end of 1st layer, continue to wind the next layer from right to left. At the end of 2nd layer, continue to wind the next layer from left to right. On the final layer, spread the winding evenly across entire bobbin. Finish this winding on pin(s) 1.

Add 3 layers of tape, item [3], for insulation.

### Core Assembly

Assemble and secure core halves. Item [1].

### Varnish

Dip varnish uniformly in item [4]. Do not vacuum impregnate.

## Comments

1. Pins 2 and 3 are electrically shorted to each other on the PCB via a copper trace.
2. Use of a grounded flux-band around the core may improve the EMI performance.
3. For non margin wound transformers use triple insulated wire for all secondary windings.

## Materials

Item	Description
[1]	Core: ETD44/22/15, 3F3, gapped for ALG of 37 nH/T <sup>2</sup>
[2]	Bobbin: Generic, 9 pri. + 9 sec.
[3]	Barrier Tape: Polyester film [1 mil (25 µm) base thickness], 29.50 mm wide
[4]	Varnish
[5]	Magnet Wire: 24 AWG (0.55 mm), Solderable Double Coated
[6]	Triple Insulated Wire: 24 AWG (0.55 mm)
[7]	Magnet Wire: 25 AWG (0.45 mm), Solderable Double Coated

## Electrical Test Specifications

Parameter	Condition	Spec
Electrical Strength, VAC	60 Hz 1 second, from pins 1,2,3,4,5,6 to pins 10,11.	3000
Nominal Primary Inductance, µH	Measured at 1 V pk-pk, typical switching frequency, between pin 1 to pin 4, with all other Windings open.	165
Tolerance, ±%	Tolerance of Primary Inductance	10.0
Maximum Primary Leakage, µH	Measured between Pin 1 to Pin 4, with all other Windings shorted.	2.47

Although the design of the software considered safety guidelines, it is the user's responsibility to ensure that the user's power supply design meets all applicable safety requirements of user's product.



	<b>Description</b>	<b>Fix</b>	<b>Ref. #</b>
	<i>Peak primary current exceeds device current limit.</i>	<i>Select larger PI device, increase minimum input voltage (VACMIN or VDCMIN), increase reflected output voltage (VOR), decrease KP, increase input capacitor (CIN) if applicable.</i>	210
	<i>Transformer windings do not fit in the winding window</i>	<i>Use a larger transformer</i>	712
	<i>Gap length too big.</i>	<i>Decrease transformer size, decrease secondary turns (NS), decrease KP.</i>	217
	<i>PI device may be too small for continuous output power.</i>	<i>Select larger PI device.</i>	207
	<i>Drain voltage close to BVDSS at maximum OV threshold.</i>	<i>Verify BVDSS during line surge, decrease VUVON_MAX or reduce VOR.</i>	237
	<i>Resistor value of RF2 is too large and may not provide enough bias for error amplifier.</i>	<i>Decrease RF2</i>	606
	<i>Peak flux density is low but design will work.</i>	<i>Choose smaller core size, decrease secondary turns (NS), decrease reflected output voltage (VOR), decrease KP.</i>	220